

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method of forming an integrated circuit, including forming a dielectric film, the method comprising:[(,)]  
~~providing a substrate;~~  
providing forming a carbon doped oxide (CDO) CDO film on the a substrate;[(,)]  
and  
treating the CDO film with an electron beam.
2. (Currently Amended) The method of claim 1, wherein ~~the~~ an energy of ~~the~~ electrons in the electron beam is about 3 keV or greater.
3. (Currently Amended) The method of claim 1, wherein ~~the~~ an energy of ~~the~~ electrons in the electron beam is about 8 keV or greater.
4. (Currently Amended) The method of claim 1, wherein ~~the~~ an energy of ~~the~~ electrons in the electron beam is determined such that ~~the~~ a predicted Kanaya-Okayama range of the electrons exceeds ~~the~~ a thickness of the CDO film.

5. (Currently Amended) The method of claim 1, further comprising:[,]  
preparing the CDO film on the substrate by using chemical vapor deposition.
6. (Currently Amended) The method of claim 1, wherein the dielectric film is an interlevel dielectric film, and the method further comprises: comprising [,]  
preparing a damascene structure in the CDO film.
7. (Currently Amended) The method of claim 6, further comprising:[,]  
filling the damascene structure with a metal.
8. (Currently Amended) The method claim 7, further comprising:[,]  
removing excess metal by using chemical[,]  
mechanical polishing (CMP).
9. (Currently Amended) The method of claim 8, wherein the metal is comprises copper.
- 10 to 28. (Cancelled)
29. (New) A method of forming a dielectric, comprising:  
forming a carbon doped oxide (CDO) film on a substrate; and  
treating the CDO film with an electron beam.

30. (New) The method of claim 29, wherein an energy of electrons in the electron beam is about 3 keV or greater.

31. (New) The method of claim 29, wherein an energy of electrons in the electron beam is about 8 keV or greater.

32. (New) The method of claim 29, wherein an energy of electrons in the electron beam is determined such that a predicted Kanaya-Okayama range of the electrons exceeds a thickness of the CDO film.

33. (New) The method of claim 29, further comprising:  
preparing the CDO film on the substrate by using chemical vapor deposition.

34. (New) The method of claim 29, wherein the dielectric comprises an interlevel dielectric film, and the method further comprises:  
preparing a damascene structure in the CDO film.

35. (New) The method of claim 34, further comprising:  
filling the damascene structure with a metal.

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Serial No. : 10/161,104  
Filed : Herewith  
Page : 6

Attorney's Docket No.: 10559-586003  
Intel Ref.: P12767D

36. (New) The method claim 35, further comprising:  
removing excess metal by using chemical mechanical polishing (CMP).
37. (New) The method of claim 36, wherein the metal comprises copper.